SOT89 PNP SILICON PLANAR MEDIUM POWER HIGH PERFORMANCE TRANSISTOR

FCX591

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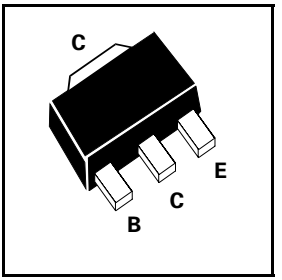

PARTMARKING DETAIL - P1
COMPLEMENTARY TYPE - FCX491

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-2	A
Continuous Collector Current	I_C	-1	A
Base Current	I_B	-200	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	1	W
Operating and Storage Temperature Range	T_j:T_{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	-80		V	I_C=-100μA, I_E=0
	$V_{(BR)CEO}$	-60		V	I_C=-10mA, I_B=0*
	$V_{(BR)EBO}$	-5		V	I_E=-100μA, I_C=0
Collector Cut-Off Current	I_{CBO}		-100	nA	V_{CB}=-60V
Collector -Emitter Cut-Off Current	I_{CES}		-100	nA	V_{CES}=-60V
Emitter Cut-Off Current	I_{EBO}		-100	nA	V_{EB}=-4V, I_C=0
Saturation Voltages	$V_{CE(sat)}$		-0.3 -0.6	V V	I_C=-500mA, I_B=-50mA* I_C=-1A, I_B=-100mA*
	$V_{BE(sat)}$		-1.2	V	I_C=-1A, I_B=-100mA*
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-1.0	V	I_C=-1A, V_{CE}=-5V*
Static Forward Current Transfer Ratio	h_{FE}	100 100 80 15	300		I_C=-1mA, V_{CE}=-5V* I_C=-500mA, V_{CE}=-5V* I_C=-1A, V_{CE}=-5V* I_C=-2A, V_{CE}=-5V*
Transition Frequency	f_T	150		MHz	I_C=-50mA, V_{CE}=-10V f=100MHz
Output Capacitance	C_{obo}		10	pF	V_{CB}=-10V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%
For typical Characteristics graphs see FMMT591 datasheet

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